

1. General description

Planar passivated four quadrant triac in a SOT428 (DPAK) surface-mountable plastic package intended for use in general purpose bidirectional switching and phase control applications.

2. Features and benefits

- High blocking voltage capability
- Least sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

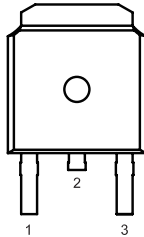

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 102\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	65	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	-	71	A
T_j	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7	-	5	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7	-	8	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 7	-	11	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ °C}$; Fig. 7	-	30	100	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9	-	5	40	mA
V_T	on-state voltage	$I_T = 10\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	1.3	1.65	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	200	250	-	V/ μ s
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400\text{ V}$; $T_j = 95\text{ °C}$; $dI_{com}/dt = 3.6\text{ A/ms}$; $I_T = 8\text{ A}$; gate open circuit	10	20	-	V/ μ s

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT137S-600G	TO252	BT137S-600G,118	Reel	2500	TO252N	07-Mar-2025
					TO252Q	05-Mar-2025

Type number	Marking codes	
	Assembly factory: N	Assembly factory: Q
BT137S-600G	137S6G PJNxxxx xx	137S6G PQxxxx xx

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 102\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	65	A
		full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 16.7\text{ ms}$	-	71	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	21	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 200\text{ mA}$	-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		-	125	$^{\circ}\text{C}$

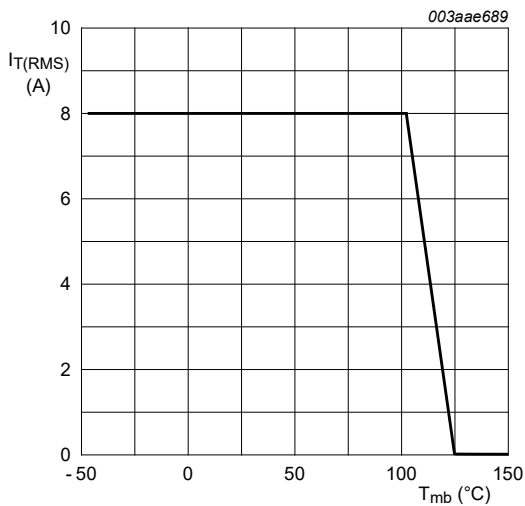
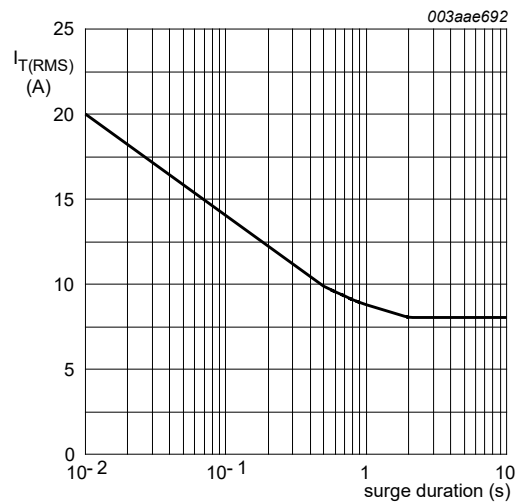


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



$f = 50\text{ Hz}$
 $T_{mb} \leq 102\text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

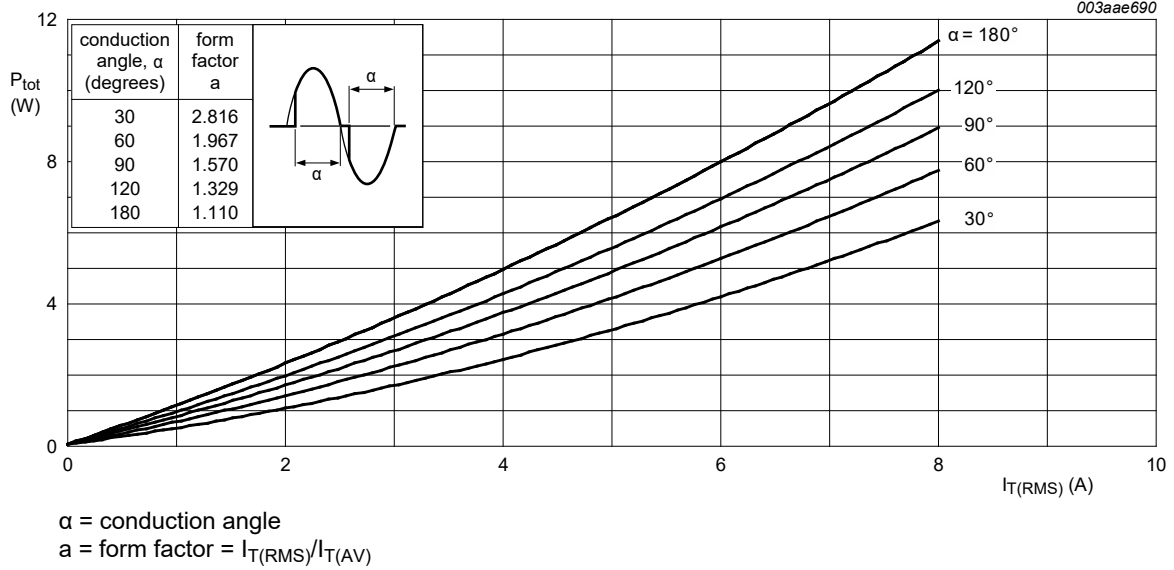


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

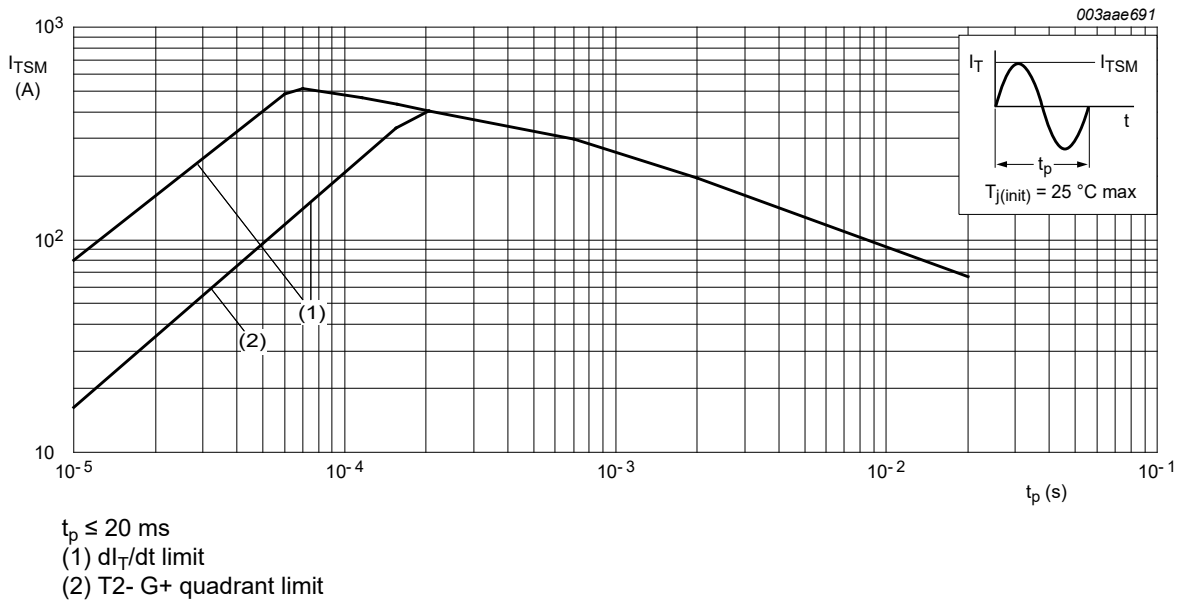


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

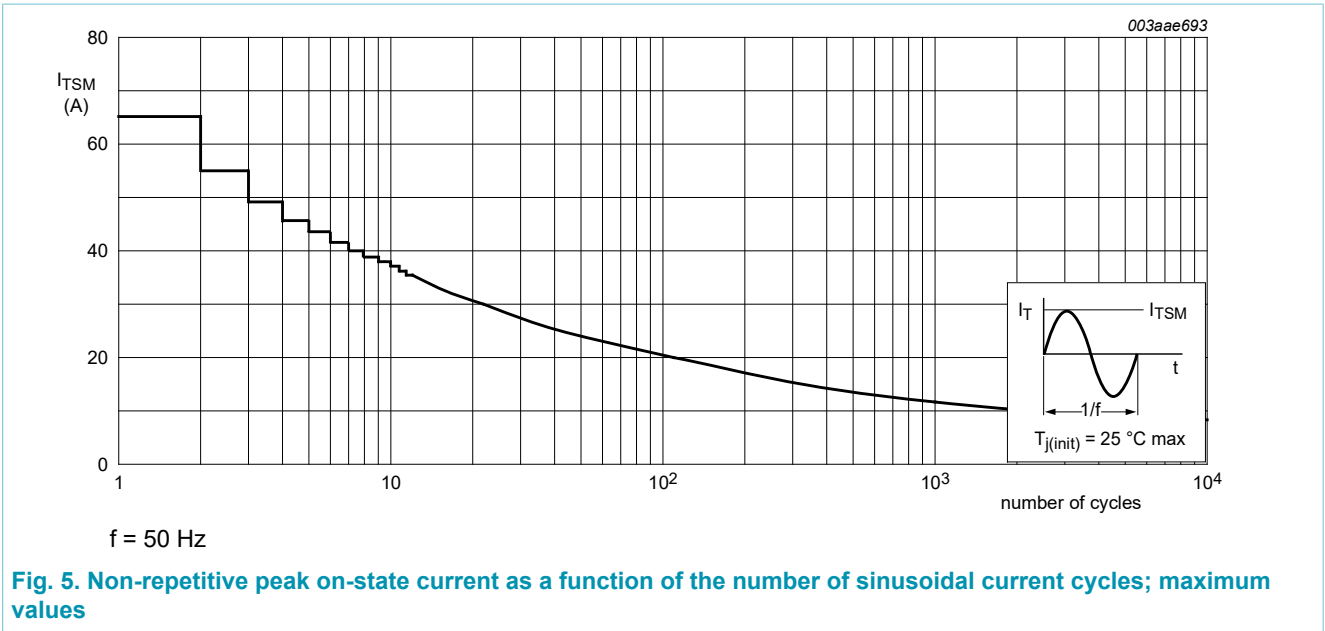


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	half cycle; Fig. 6	-	-	2.4	K/W
		full cycle; Fig. 6	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	PCB (FR4) mounted; minimum pad sizes	-	75	-	K/W

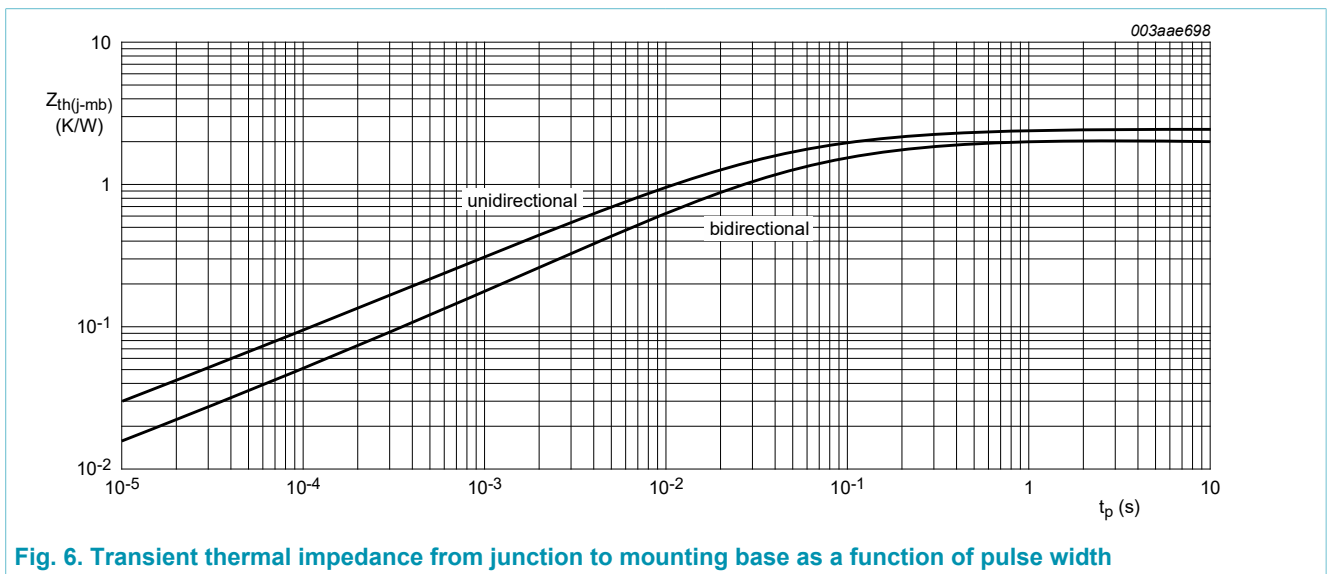


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7	-	5	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7	-	8	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 7	-	11	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ °C}$; Fig. 7	-	30	100	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 8	-	7	45	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 8	-	16	60	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 8	-	5	45	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ °C}$; Fig. 8	-	7	60	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9	-	5	40	mA
V_T	on-state voltage	$I_T = 10\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11	-	0.7	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$; Fig. 11	0.25	0.4	-	V
I_D	off-state current	$V_D = 600\text{ V}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	200	250	-	V/ μ s
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400\text{ V}$; $T_j = 95\text{ °C}$; $dI_{com}/dt = 3.6\text{ A/ms}$; $I_T = 8\text{ A}$; gate open circuit	10	20	-	V/ μ s

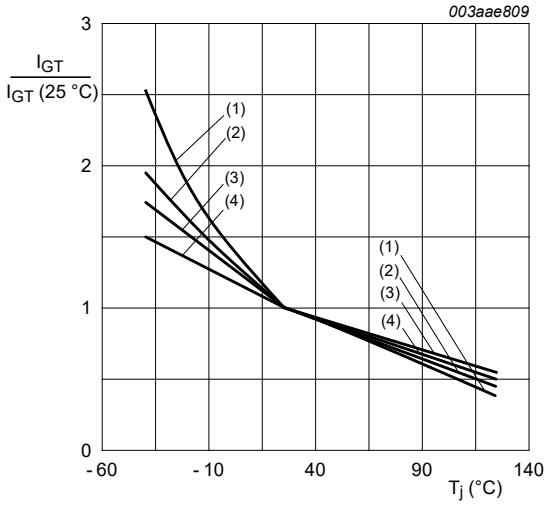


Fig. 7. Normalized gate trigger current as a function of junction temperature

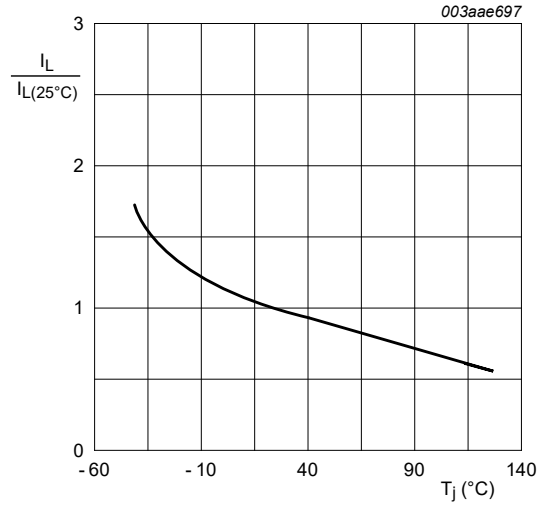


Fig. 8. Normalized latching current as a function of junction temperature

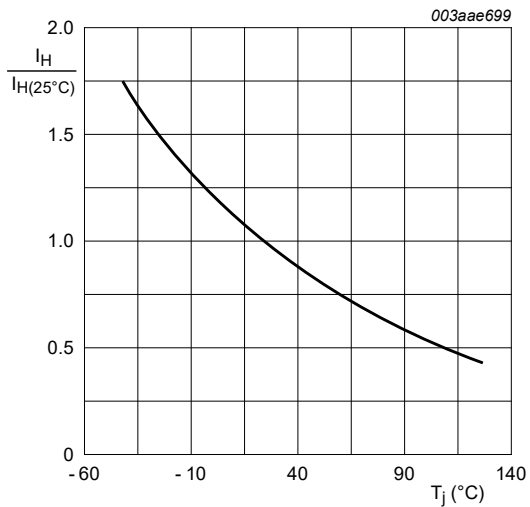
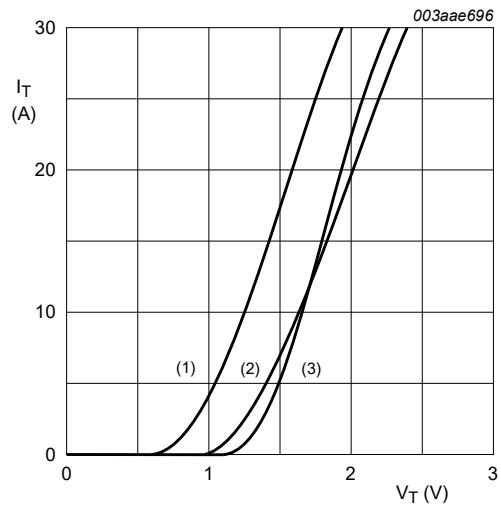


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.264\text{ V}$
 $R_s = 0.038\ \Omega$
 (1) $T_j = 125^\circ\text{C}$; typical values
 (2) $T_j = 125^\circ\text{C}$; maximum values
 (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

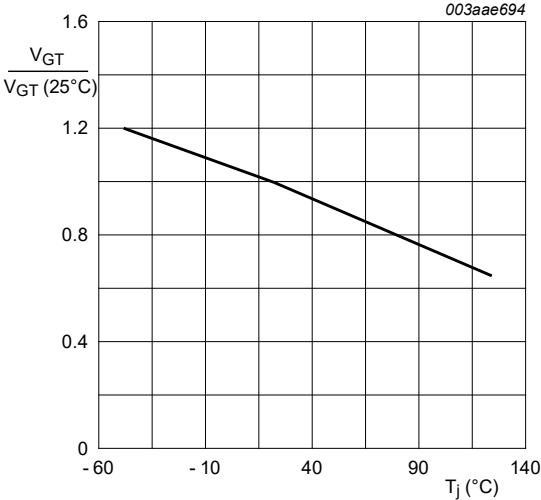
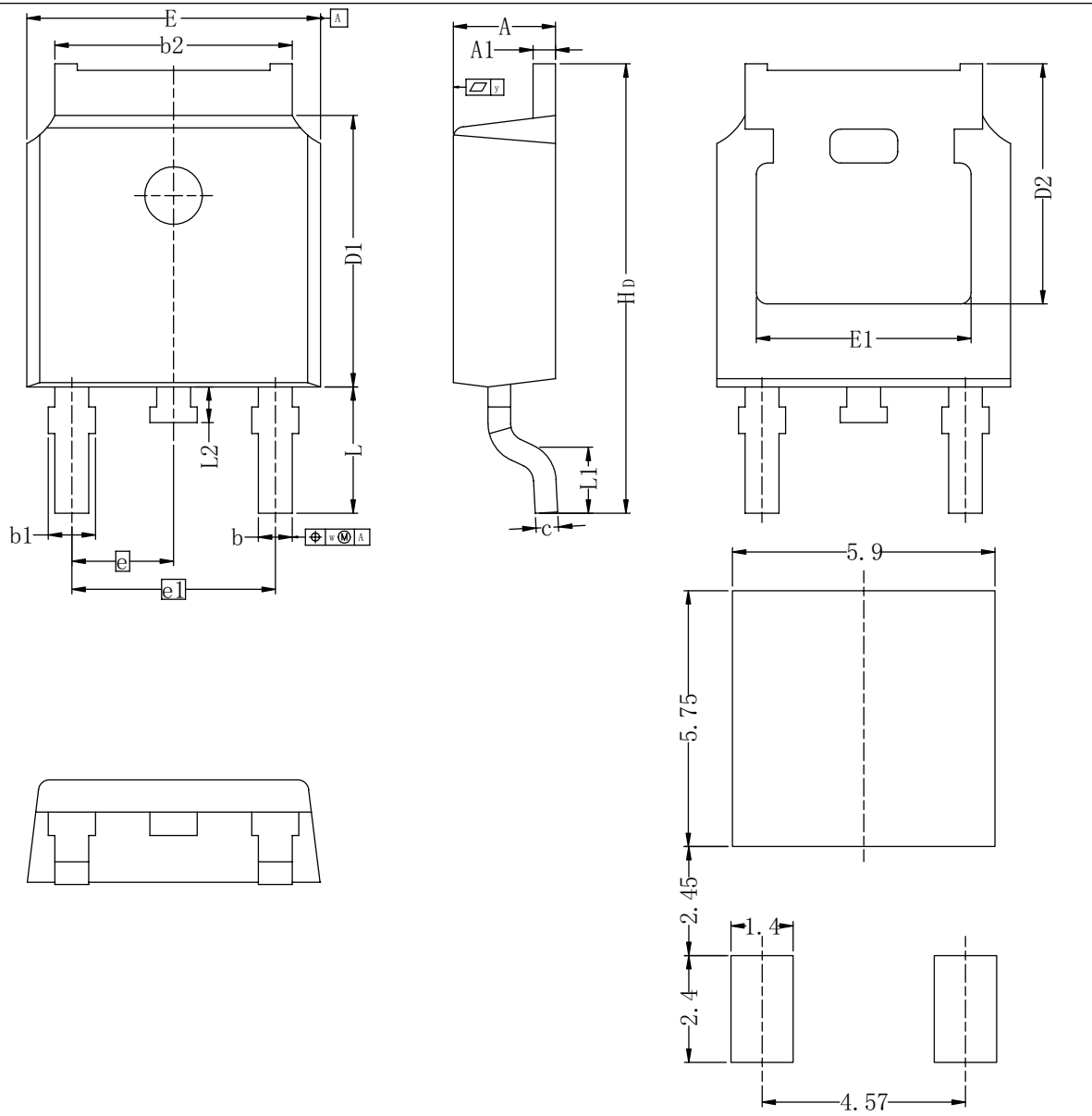


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

Assembly factory: N

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)



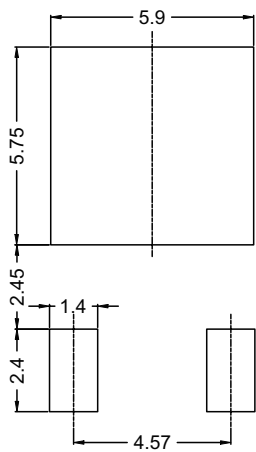
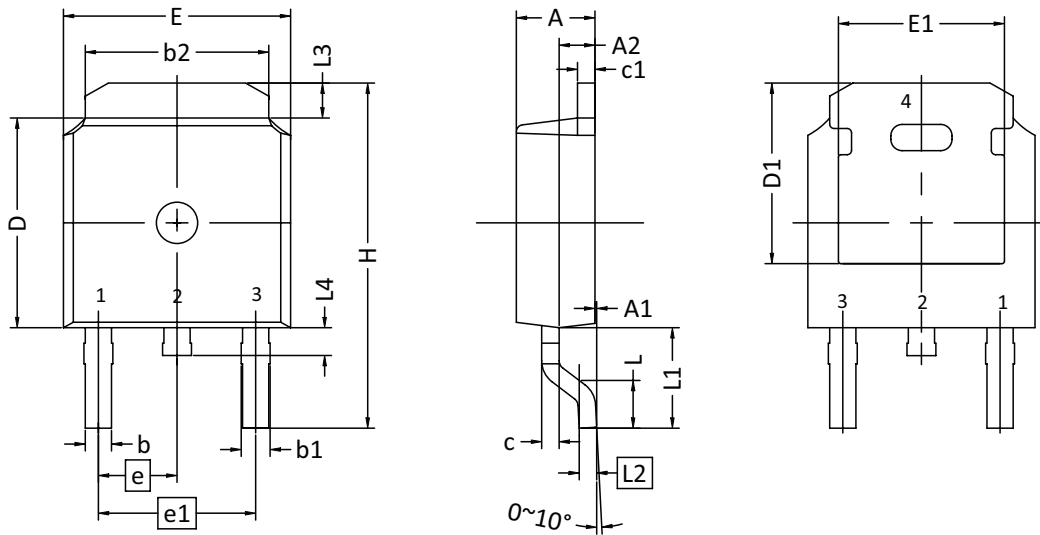
Recommended Footprint

Unit	A	A1	b	b1	b2	c	D1	D2	E	E1	e	e1	H _D	L	L1	L2	w	y
min	2.22	0.46	0.71	0.72	5.00	0.20	5.98	4.00	6.47	4.45	2.285	4.57	9.60	2.90 (Ref.)	0.50	0.50	0.20	
nom																		
max	2.38	0.93	0.89	1.10	5.46	0.56	6.22	---	6.73	---			10.40		---	0.90		0.20

Assembly factory: Q

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

TO252



Recommended Footprint

SYMBOLS	DIMENSION IN MM		
	MIN	NOM	MAX
A	2.184	2.286	2.400
A1	0.000	---	0.200
A2	0.889	1.041	1.170
b	0.635	0.762	0.889
b1	0.680	0.840	1.143
b2	4.953	5.340	5.500
c	0.450	0.508	0.610
c1	0.450	0.508	0.630
D	5.969	6.096	6.223
D1	5.210	5.249	5.380
E	6.350	6.604	6.800
E1	4.318	4.826	4.920
e	2.286BSC		
e1	4.572BSC		
H	9.398	10.033	10.500
L	1.270	1.520	2.032
L1	2.921REF		
L2	0.408	0.508	0.608
L3	0.889	1.016	1.270
L4	0.600	---	1.016

11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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12. Contents

1. General description.....	1
2. Features and benefits.....	1
3. Applications.....	1
4. Quick reference data.....	1
5. Pinning information.....	2
6. Ordering information.....	2
7. Limiting values.....	3
8. Thermal characteristics.....	6
9. Characteristics.....	7
10. Package outline.....	10
11. Legal information.....	11

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